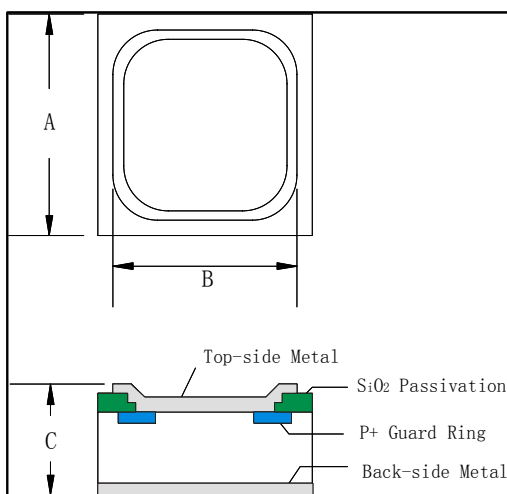


SCHOTTKY DIE SPECIFICATION	TYPE: SB545
General Description: 45 V 5 A (<input checked="" type="checkbox"/> Standard <input type="checkbox"/> Low) VF ,	(<input checked="" type="checkbox"/> Single <input type="checkbox"/> Dual) Anode

ELECTRICAL CHARACTERISTICS	SYM	Spec. Limit	Die Sort	UNIT
DC Blocking Voltage: Ir=1mA(for wafer form)	VRRM	45		Volt
Average Rectified Forward Current	IFAV	5		Amp
Maximum Instantaneous Forward Voltage				
@ 5 Ampere, Ta=25°C	VF MAX	0.520		Volt
Reverse current				
@ VR= 47 Volt, Ta=25°C	IR MAX	0.200		mA
MAXIMUM RATINGS				
Nonrepetitive Peak Surge Current	IFSM	150		Amp
Operating Junction Temperature	Tj	125		°C
Storage Temperature	TSTG	-50 to +150		°C

Specifications apply to die only. Actual performance may degrade when assembled.
 We do not guarantee device performance after assembly.
 Data sheet information is subjected to change without notice.

DICE OUTLINE DRAWING



DIM	ITEM	μ m	Mil
A	Die Size	1778	70.00
B	Top Metal Pad Size	1674	65.90
C	Thickness (Min)	280	11.00
	Thickness (Max)	300	11.80

PS:
 (1)Cutting street width is around 16 μ m (0.62mil).
 (2)Both of top-side and back-side metals are Ti/Ni/Ag.